TOSHIBA Power Transistor Module
Silicon NPN&PNP Epitaxial Type (Four Darlington Power Transistors in One)

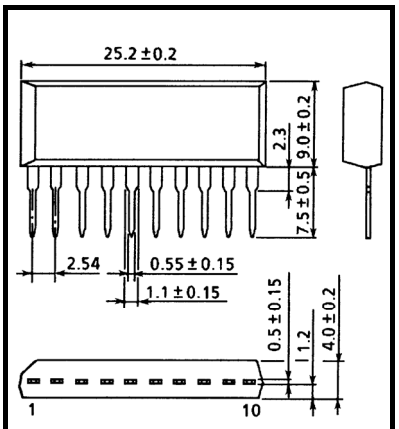
MP4006

Industrial Applications

High Power Switching Applications.

Hammer Drive, Pulse Motor Drive and Inductive Load Switching.

Unit: mm



1, 10 EMITTER
2, 4, 6, 8 BASE
3, 5, 7, 9 COLLECTOR
(PIN 1 AND PIN 10 ARE DISCONNECTED INTERNALLY)

JEDEC	—
JEITA	—
TOSHIBA	2-25A1B

Weight: 2.1 g (typ.)

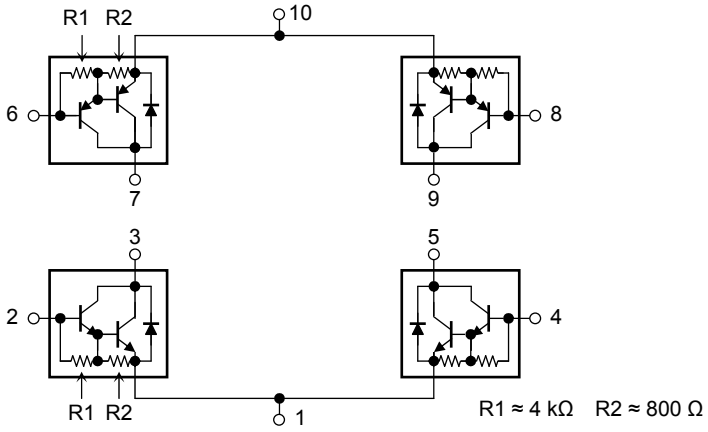
- Small package by full molding (SIP 10 pins)
- High collector power dissipation (4-device operation)
  : $I_{C\ (DC)}$ = ±2 A (max)
- High DC current gain: h_{FE} = 2000 (min) (V_{CE} = ±2 V, I_C = ±1 A)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating		Unit
			NPN	PNP	
Collector-base voltage		V_{CBO}	80	−80	V
Collector-emitter voltage		V_{CEO}	80	−80	V
Emitter-base voltage		V_{EBO}	8	−8	V
Collector current	DC	I_C	2	−2	A
	Pulse	I_{CP}	3	−3	
Continuous base current		I_B	0.5	−0.5	A
Collector power dissipation (1-device operation)		P_C	2.0		W
Collector power dissipation (4-device operation)		P_T	4.0		W
Junction temperature		T_j	150		°C
Storage temperature range		T_{stg}	−55 to 150		°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

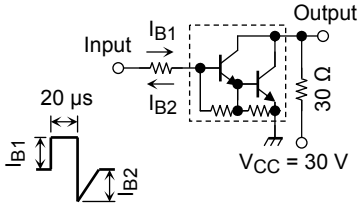
Array Configuration



Thermal Characteristics

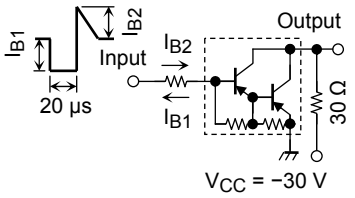
Characteristics	Symbol	Max	Unit
Thermal resistance from junction to ambient (4-device operation, Ta = 25°C)	$\Sigma R_{th\ (j\text{-}a)}$	31.3	°C/W
Maximum lead temperature for soldering purposes (3.2 mm from case for 10 s)	T_L	260	°C

Electrical Characteristics (Ta = 25°C) (NPN transistor)

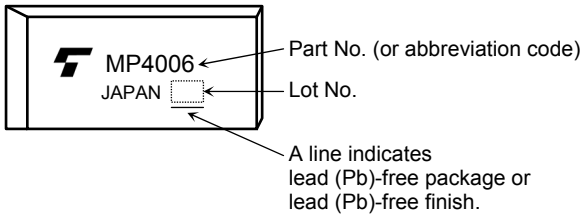
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	V_{CB} = 80 V, I_E = 0 A	—	—	10	μA
Collector cut-off current		I_{CEO}	V_{CE} = 80 V, I_B = 0 A	—	—	10	μA
Emitter cut-off current		I_{EBO}	V_{EB} = 8 V, I_C = 0 A	0.8	—	4.0	mA
Collector-base breakdown voltage		$V_{(BR)\ CBO}$	I_C = 1 mA, I_E = 0 A	80	—	—	V
Collector-emitter breakdown voltage		$V_{(BR)\ CEO}$	I_C = 10 mA, I_B = 0 A	80	—	—	V
DC current gain		h_{FE}	V_{CE} = 2 V, I_C = 1 A	2000	—	—	—
Saturation voltage	Collector-emitter	$V_{CE\ (sat)}$	I_C = 1 A, I_B = 1 mA	—	—	1.5	V
	Base-emitter	$V_{BE\ (sat)}$	I_C = 1 A, I_B = 1 mA	—	—	2.0	
Transition frequency		f_T	V_{CE} = 2 V, I_C = 0.5 A	—	100	—	MHz
Collector output capacitance		C_{ob}	V_{CB} = 10 V, I_E = 0 A, f = 1 MHz	—	20	—	pF
Switching time	Turn-on time	t_{on}		—	0.4	—	μs
	Storage time	t_{stg}		—	4.0	—	
	Fall time	t_f		—	0.6	—	

$I_{B1} = -I_{B2}$ = 1 mA, duty cycle ≤ 1%

Electrical Characteristics (Ta = 25°C) (PNP transistor)

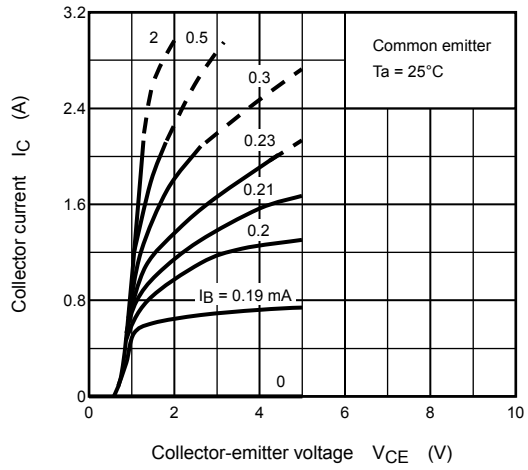
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	V_{CB} = −80 V, I_E = 0 A	—	—	−10	μA
Collector cut-off current		I_{CEO}	V_{CE} = −80 V, I_B = 0 A	—	—	−10	μA
Emitter cut-off current		I_{EBO}	V_{EB} = −8 V, I_C = 0 A	−0.8	—	−4.0	mA
Collector-base breakdown voltage		$V_{(BR)\ CBO}$	I_C = −1 mA, I_E = 0 A	−80	—	—	V
Collector-emitter breakdown voltage		$V_{(BR)\ CEO}$	I_C = −10 mA, I_B = 0 A	−80	—	—	V
DC current gain		h_{FE}	V_{CE} = −2 V, I_C = −1 A	2000	—	—	—
Saturation voltage	Collector-emitter	$V_{CE\ (sat)}$	I_C = −1 A, I_B = −1 mA	—	—	−1.5	V
	Base-emitter	$V_{BE\ (sat)}$	I_C = −1 A, I_B = −1 mA	—	—	−2.0	
Transition frequency		f_T	V_{CE} = −2 V, I_C = −0.5 A	—	50	—	MHz
Collector output capacitance		C_{ob}	V_{CB} = −10 V, I_E = 0 A, f = 1 MHz	—	30	—	pF
Switching time	Turn-on time	t_{on}		—	0.4	—	μs
	Storage time	t_{stg}		—	2.0	—	
	Fall time	t_f		—	0.4	—	
			$-I_{B1} = I_{B2}$ = 1 mA, duty cycle ≤ 1%				

Marking

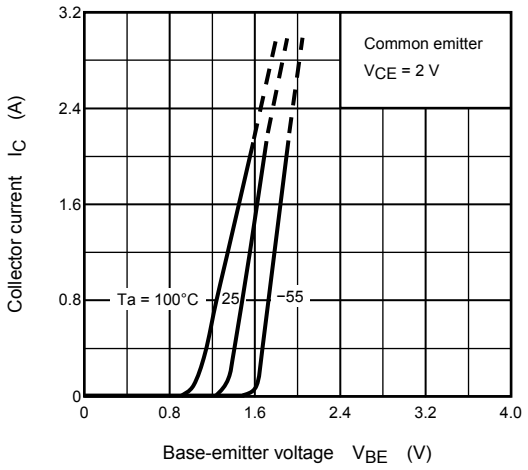


(NPN transistor)

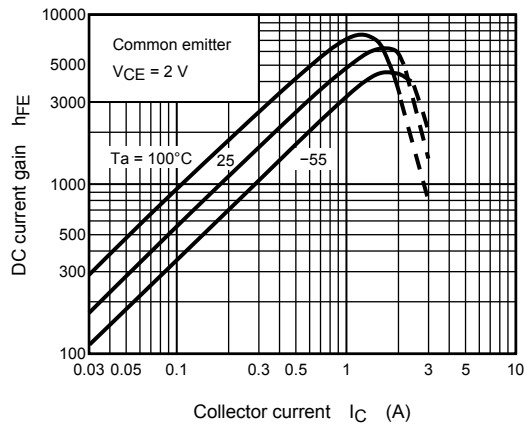
$I_C - V_{CE}$



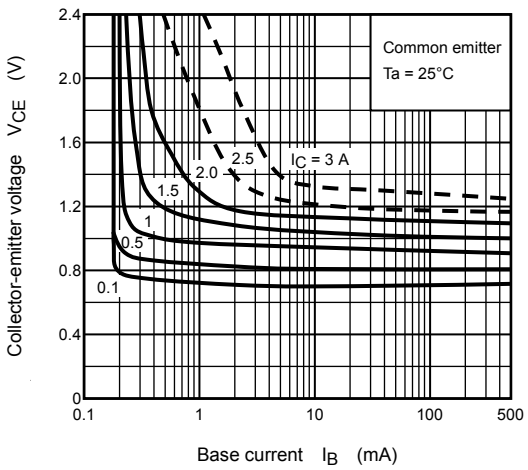
$I_C - V_{BE}$



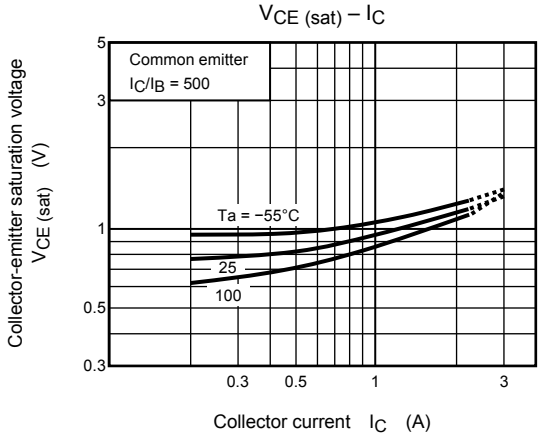
$h_{FE} - I_C$



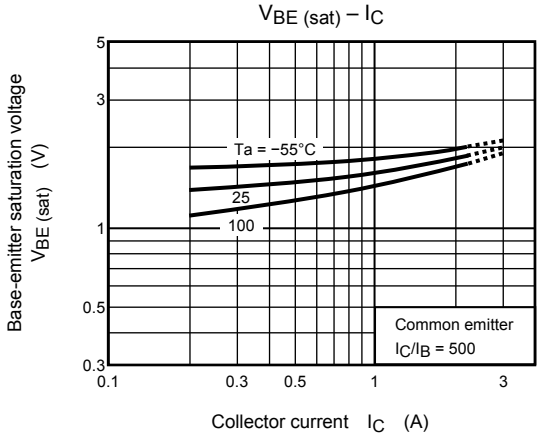
$V_{CE} - I_B$



$V_{CE\ (sat)} - I_C$

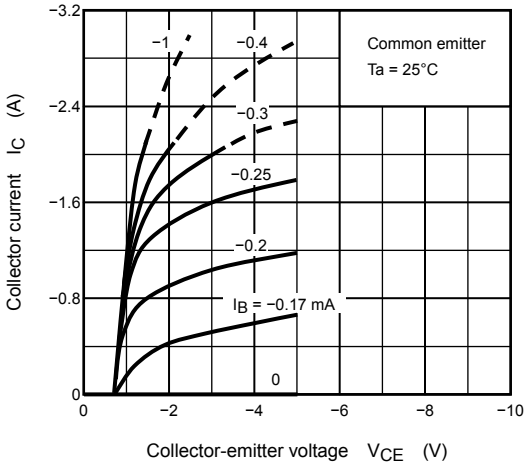


$V_{BE\ (sat)} - I_C$

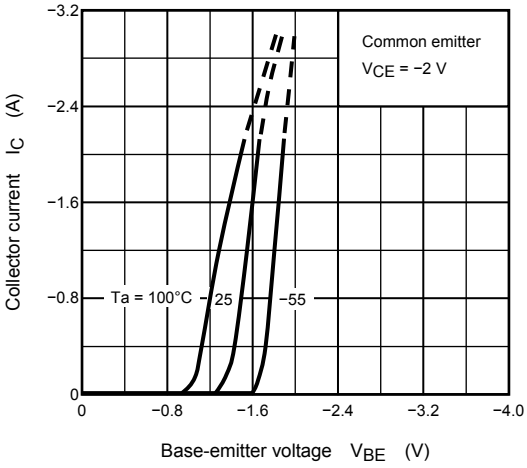


(PNP transistor)

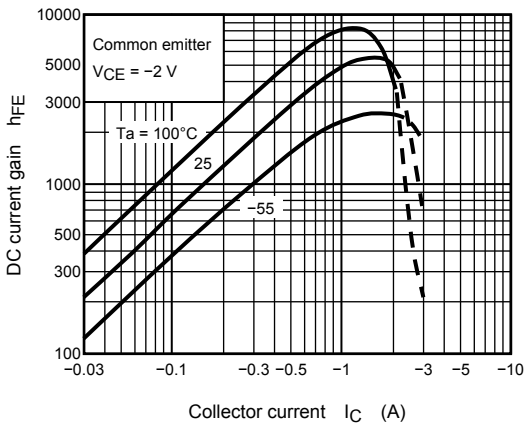
$I_C - V_{CE}$



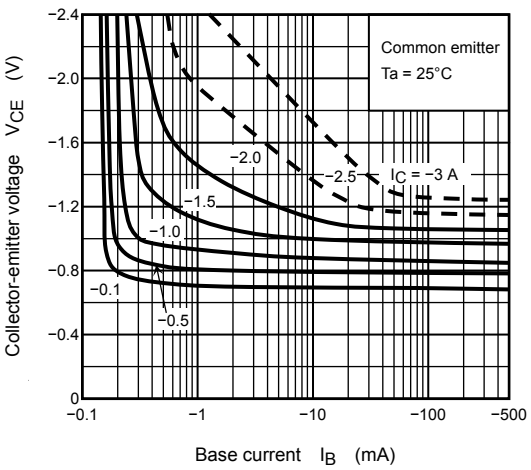
$I_C - V_{BE}$



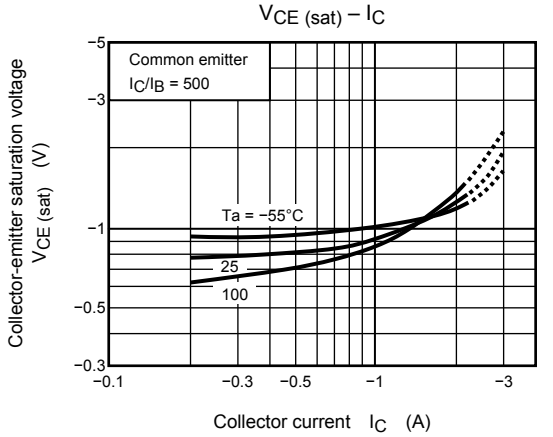
$h_{FE} - I_C$



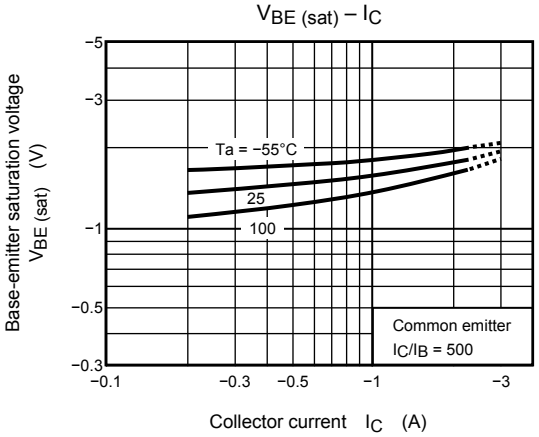
$V_{CE} - I_B$



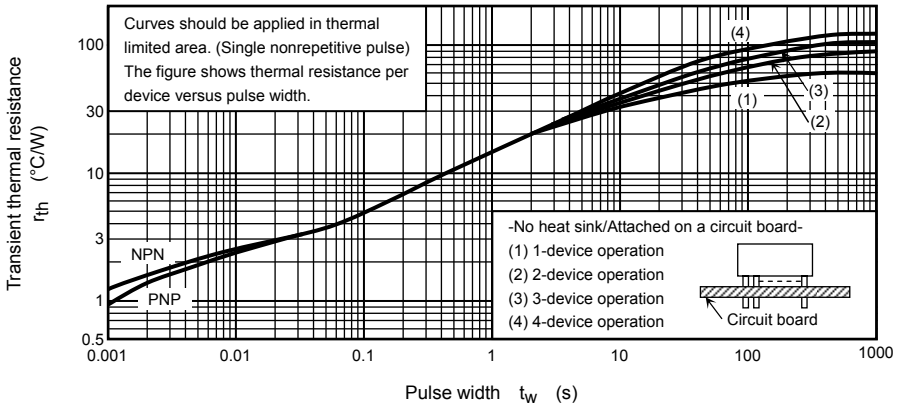
$V_{CE\ (sat)} - I_C$



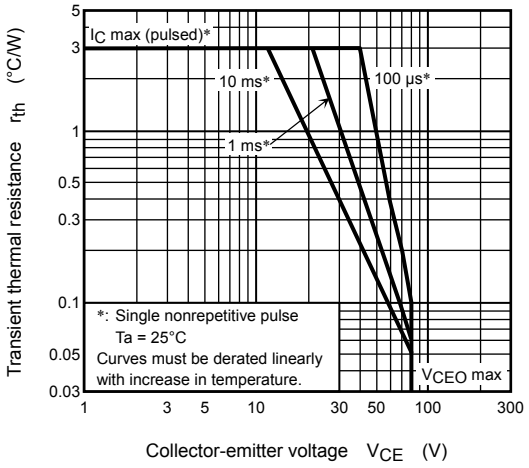
$V_{BE\ (sat)} - I_C$



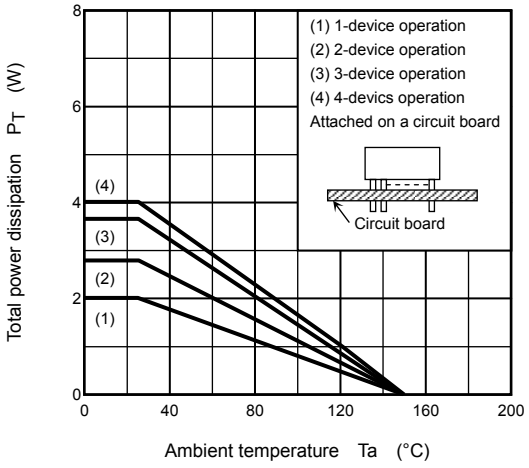
$r_{th} - t_w$



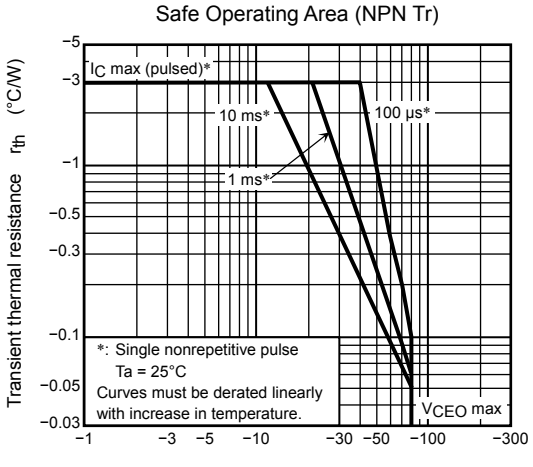
Safe Operating Area (NPN Tr)



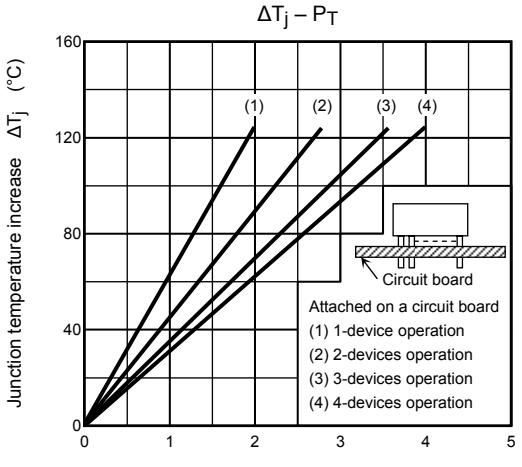
P_T – Ta



Safe Operating Area (NPN Tr)



$\Delta T_j - P_T$



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